Features

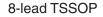
- Write Protect Pin for Hardware Data Protection
 - Utilizes Different Array Protection Compared to the AT24C04B
- Low-voltage and Standard-voltage Operation
 - $-1.8 (V_{CC} = 1.8V \text{ to } 5.5V)$
- Internally Organized 512 x 8 (4K)
- Two-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bidirectional Data Transfer Protocol
- 1 MHz (5V) and 400 kHz (1.8V, 2.5V, 2.7V) Clock Rate
- 16-byte Page
- Partial Page Writes Allowed
- Self-timed Write Cycle (5 ms Max)
- High Reliability
 - Endurance: One Million Write Cycles
 - Data Retention: 100 Years
- 8-lead PDIP, 8-lead JEDEC SOIC and 8-lead TSSOP Packages
- Die Sales: Wafer Form, Tape and Reel, and Bumped Wafers

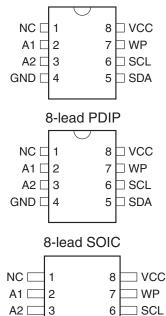
Description

The AT24HC04B provides 4096 bits of serial electrically erasable and programmable read-only memory (EEPROM) organized as 512 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The AT24HC04B is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC and 8-lead TSSOP packages and is accessed via a two-wire serial interface. In addition, the entire family is available in 1.8V (1.8V to 5.5V) version.

Table 0-1. Pin Configuration

Pin Name	Function
A1, A2	Address Inputs
SDA	Serial Data
SCL	Serial Clock Input
WP	Write Protect
NC	No-connect





5

□ SDA



GND [



Two-wire Serial EEPROM

4K (512 x 8)

AT24HC04B



Absolute Maximum Ratings*

Operating Temperature40°C to +125°C
Storage Temperature65°C to +150°C
Voltage on Any Pin with Respect to Ground1.0V to +7.0V
Maximum Operating Voltage
DC Output Current5.0 mA

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 0-1. Block Diagram VCC -GND ---WP -**START** SCL -**STOP** SDA -**LOGIC SERIAL** H.V. PUMP/TIMING CONTROL **LOGIC** LOAD COMP DATA RECOVERY **DEVICE ADDRESS** LOAD INC COMPARATOR DEC R/W DATA WORD **EEPROM** ADDR/COUNTER Y DEC **SERIAL MUX** $\mathsf{D}_{\underline{\scriptscriptstyle{\mathsf{I}}\!\mathsf{N}}}$ $\mathsf{D}_{\mathrm{out}}\!/\mathsf{ACK}$ LOGIC



2. Memory Organization

AT24HC04B, **4K SERIAL EEPROM**: The 4K is internally organized with 32 pages of 16 bytes each. Random word addressing requires an 9-bit data word address.

Table 2-1. Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_{AI} = 25$ °C, f = 1.0 MHz, $V_{CC} = +1.8$ V

Symbol Test Condition		Max	Units	Conditions
C _{I/O}	Input/Output Capacitance (SDA)	8	pF	$V_{I/O} = 0V$
C _{IN}	Input Capacitance (A ₀ , A ₁ , A ₂ , SCL)	6	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

Table 2-2. DC Characteristics

Applicable over recommended operating range from: $T_{Al} = -40$ °C to +85°C, $V_{CC} = +1.8$ V to +5.5V (unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
V _{CC1}	Supply Voltage		1.8		5.5	V
V _{CC2}	Supply Voltage		2.5		5.5	V
V _{CC3}	Supply Voltage		2.7		5.5	V
V _{CC4}	Supply Voltage		4.5		5.5	V
I _{CC}	Supply Current V _{CC} = 5.0V	READ at 100 kHz		0.4	1.0	mA
I _{CC}	Supply Current V _{CC} = 5.0V	WRITE at 100 kHz		2.0	3.0	mA
I _{SB1}	Standby Current V _{CC} = 1.8V	$V_{IN} = V_{CC}$ or V_{SS}		0.6	3.0	μΑ
I _{SB2}	Standby Current V _{CC} = 2.5V	$V_{IN} = V_{CC}$ or V_{SS}		1.4	4.0	μΑ
I _{SB3}	Standby Current V _{CC} = 2.7V	$V_{IN} = V_{CC}$ or V_{SS}		1.6	4.0	μΑ
I _{SB4}	Standby Current V _{CC} = 5.0V	$V_{IN} = V_{CC}$ or V_{SS}		8.0	18.0	μΑ
I _{LI}	Input Leakage Current	$V_{IN} = V_{CC}$ or V_{SS}		0.10	3.0	μΑ
I _{LO}	Output Leakage Current	$V_{OUT} = V_{CC} \text{ or } V_{SS}$		0.05	3.0	μΑ
V _{IL}	Input Low Level (1)		-0.6		V _{CC} x 0.3	V
V _{IH}	Input High Level (1)		V _{CC} x 0.7		V _{CC} + 0.5	V
V _{OL2}	Output Low Level V _{CC} = 3.0V	I _{OL} = 2.1 mA			0.4	V
V _{OL1}	Output Low Level V _{CC} = 1.8V	I _{OL} = 0.15 mA			0.2	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

Table 2-3. AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = +1.8\text{V}$ to +5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted)

		1.8, 2.5, 2.7		5.0-volt		
Symbol	Parameter	Min	Max	Min	Max	Units
f _{SCL}	Clock Frequency, SCL		400		1000	kHz
t _{LOW}	Clock Pulse Width Low	1.2		0.4		μs
t _{HIGH}	Clock Pulse Width High	0.6		0.4		μs
t _I	Noise Suppression Time		50		40	ns
t _{AA}	Clock Low to Data Out Valid	0.1	0.9	0.05	0.55	μs
t _{BUF}	Time the bus must be free before a new transmission can start	1.2		0.5		μs
t _{HD.STA}	Start Hold Time	0.6		0.25		μs
t _{SU.STA}	Start Setup Time	0.6		0.25		μs
t _{HD.DAT}	Data In Hold Time	0		0		μs
t _{SU.DAT}	Data In Setup Time	100		100		ns
t _R	Inputs Rise Time ⁽¹⁾		0.3		0.3	μs
t _F	Inputs Fall Time ⁽¹⁾		300		100	ns
t _{SU.STO}	Stop Setup Time	0.6		.25		μs
t _{DH}	Data Out Hold Time	50		50		ns
t _{WR}	Write Cycle Time		5		5	ms
Endurance ⁽¹⁾	5.0V, 25°C, Byte Mode	1 Million		Write Cycles		

Note: 1. This parameter is ensured by characterization only.





7. AT24HC04B Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT24HC04B-PU (Bulk form only)	1.8	8P3	
AT24HC04BN-SH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8S1	Lead-free/Halogen-free/
AT24HC04BN-SH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8S1	Industrial Temperature
AT24HC04B-TH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8A2	(–40°C to 85°C)
AT24HC04B-TH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8A2	
AT24HC04B-W-11 ⁽³⁾	1.8	Die Sale	Industrial Temperature (-40°C to 85°C)

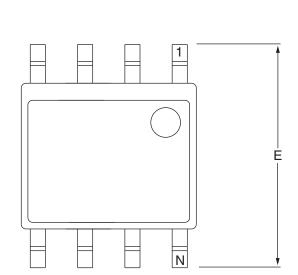
Notes: 1. "-B" denotes bulk.

- 2. "-T" denotes tape and reel. SOIC = 4K per reel. TSSOP = 5K per reel.
- 3. Available in tape and reel and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

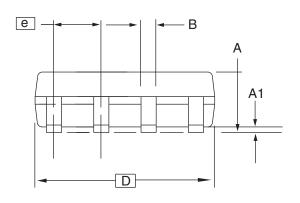
Package Type				
8P3	8-pin, 0.300" Wide, Plastic Dual Inline Package (PDIP)			
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)			
8A2	8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)			
Options				
-1.8	Low Voltage (1.8V to 5.5V)			



8S1 - JEDEC SOIC



Top View



Side View

E1 D

End View

COMMON DIMENSIONS (Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
Α	1.35	-	1.75	
A1	0.10	_	0.25	
b	0.31	_	0.51	
С	0.17	_	0.25	
D	4.80	-	5.00	
E1	3.81	-	3.99	
E	5.79	_	6.20	
е				
L	0.40	_	1.27	
Ø	0°	_	8°	

Note: These drawings are for general information only. Refer to JEDEC Drawing MS-012, Variation AA for proper dimensions, tolerances, datums, etc.

AMEL 11:

1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 **TITLE 8S1**, 8-lead (0.150" Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)

DRAWING NO. 8S1 B